L Number	Hits	Search Text	DB	Time stamp
1	131402	\$3prom ((non-volatile nonvolatile flash) adj2 memory)	USPAT;	2002/11/14 10:17
'	,51402	(((US-PGPUB;	
}			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	25292	(\$3prom ((non-volatile nonvolatile flash) adj2 memory)) and	USPAT;	2002/11/14 10:18
		(isolation STI BOX LOCOS swami)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	<u> </u>
15	376	(gate electrode) near5 damascene	USPAT;	2002/11/14 10:19
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		(20 (1) 13 (1) 13 (1) 15 (1)	IBM_TDB	2002/44/44 44/44
22	28	(\$3prom ((non-volatile nonvolatile flash) adj2 memory)) and	USPAT;	2002/11/14 14:44
		((gate electrode) near5 damascene)	US-PGPUB;	
		•	EPO; JPO;	
			DERWENT; IBM_TDB	
00		/#5022004# L#5642042# L#5707007# L#5724242# L#5752525# L	USPAT	2002/11/14 11:21
29	8	("5032881" "5643813" "5707897" "5731242" "5753525" "5767005" "6060358" "6080624").PN.	USFAI	2002/11/19 11.21
37	371	(gate or ((gate control) adj electrode)) near10 interconnect\$3	USPAT;	2002/11/14 11:40
31	3/1	near20 (simultaneous simultaneously "same time")	US-PGPUB;	2002/11/14 11:40
		liearzo (simultarieous simultarieousiy sume time)	EPO; JPO;	
			DERWENT:	
			IBM_TDB	
44	25585	remov\$3 near6 (sacrificial disposable dielectric)	USPAT;	2002/11/14 14:48
	20000	Terrovo ricaro (cacimolar aloposable alciestic)	US-PGPUB;	
			EPO; JPO;	
			DERWENT:	
			IBM TDB	
51	120	((gate electrode) near5 damascene) and (remov\$3 near6	USPAT;	2002/11/14 15:57
		(sacrificial disposable dielectric))	US-PGPUB;	
		, , , , , , , , , , , , , , , , , , , ,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
58	134986	((trench groove opening hole via patterned) near3 (dielectric	USPAT;	2002/11/14 16:50
		insulation insulating insulator sacrificial disposable	US-PGPUB;	
		removable))	EPO; JPO;	
			DERWENT;	
	55040	(1)	IBM_TDB	2002/11/14 16:51
65	55049	((trench groove opening hole via patterned) near3 (metal	USPAT; US-PGPUB;	2002/11/14 16:51
		polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3	EPO; JPO;	
		deposit\$3 form\$3)	DERWENT;	
			IBM_TDB	
72	8456	(((trench groove opening hole via patterned) near3 (dielectric	USPAT;	2002/11/14 16:50
12	0430	insulation insulating insulator sacrificial disposable	US-PGPUB;	
		removable))) same (((trench groove opening hole via	EPO; JPO;	
		patterned) near3 (metal polysilicon (polycrystalline adj (si	DERWENT;	
		silicon)))) near15 (fill\$3 deposit\$3 form\$3))	IBM TDB	
79	5988	(((trench groove opening hole via patterned) near3 (metal	USPAT;	2002/11/14 16:54
-		polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3	US-PGPUB;	
	1	deposit\$3 form\$3)) near20 (gate (gate adj electrode))	EPO; JPO;	
	1		DERWENT;	
	1		IBM_TDB	
86	12320	(((trench groove opening hole via patterned) near3 (metal	USPAT;	2002/11/14 16:56
		polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3	US-PGPUB;	
		deposit\$3 form\$3)) near20 (contact\$3 interconnect\$3)	EPO; JPO;	
			DERWENT;	1
			IBM_TDB	
L		1		

93	1628	((((trench groove opening hole via patterned) near3 (metal	USPAT;	2002/11/14 16:56
		polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3	US-PGPUB;	
		deposit\$3 form\$3)) near20 (gate (gate adj electrode))) and	EPO; JPO;	
		((((trench groove opening hole via patterned) near3 (metal	DERWENT;	
		polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3	IBM_TDB	
		deposit\$3 form\$3)) near20 (contact\$3 interconnect\$3))	_	
100	1188	((((trench groove opening hole via patterned) near3 (metal	USPAT;	2002/11/14 16:58
		polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3	US-PGPUB;	
		deposit\$3 form\$3)) near20 (gate (gate adj electrode))) same	EPO; JPO;	
		((((trench groove opening hole via patterned) near3 (metal	DERWENT;	
		polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3	IBM_TDB	
		deposit\$3 form\$3)) near20 (contact\$3 interconnect\$3))	_	
107	164	(remov\$3 near6 (sacrificial disposable dielectric)) and	USPAT;	2002/11/14 17:17
		(((((trench groove opening hole via patterned) near3 (metal	US-PGPUB;	
		polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3	EPO; JPO;	.
		deposit\$3 form\$3)) near20 (gate (gate adj electrode))) same	DERWENT;	
		((((trench groove opening hole via patterned) near3 (metal	IBM_TDB	
		polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3		
		deposit\$3 form\$3)) near20 (contact\$3 interconnect\$3)))		
114	34017	SRAM (static adj2 memory)	USPAT;	2002/11/14 17:18
			US-PGPUB;	
j ,			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
121	23	((gate electrode) near5 damascene) and (SRAM (static adj2	USPAT;	2002/11/14 17:23
		memory))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
128	464	438/259,589.ccls.	USPAT;	2002/11/14 17:24
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
135	15	438/259,589.ccls. and (damascene or inlaid inlain)	USPAT;	2002/11/14 17:26
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	